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NLX1G332

3-Input OR Gate

The NLX1G332 is an advanced high-speed 3-input CMOS OR gate in ultra-small footprint.

The NLX1G332 input structures provide protection when voltages up to 7.0 V are applied, regardless of the supply voltage.

Features

- High Speed: $t_{PD} = 2.4 \text{ ns}$ (Typ) @ $V_{CC} = 5.0 \text{ V}$
- Designed for 1.65 V to 5.5 V V_{CC} Operation
- Low Power Dissipation: $I_{CC} = 1 \mu\text{A}$ (Max) at $T_A = 25^\circ\text{C}$
- 24 mA Balanced Output Source and Sink Capability
- Balanced Propagation Delays
- Overvoltage Tolerant (OVT) Input Pins
- Ultra-Small Packages
- These are Pb-Free Devices

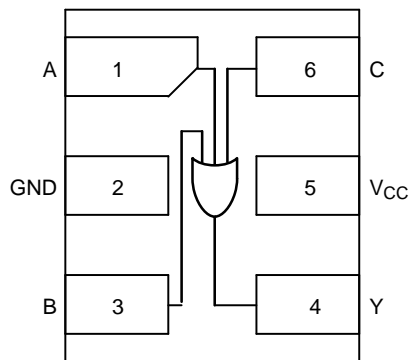


Figure 1. Pinout (Top View)

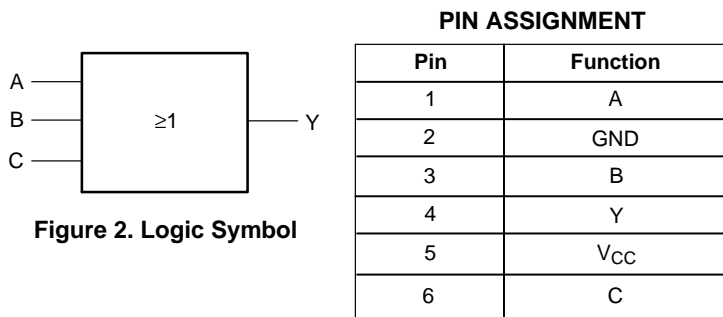


Figure 2. Logic Symbol

FUNCTION TABLE

Input			Output
A	B	C	Y
H	X	X	H
X	H	X	H
X	X	H	H
L	L	L	L

H – HIGH Logic Level

L – LOW Logic Level

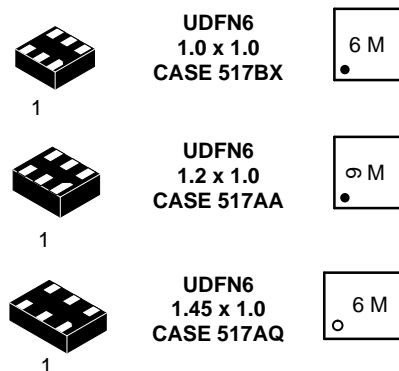
X = Either LOW or HIGH Logic Level



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MARKING DIAGRAMS



- X = Device Marking
- M = Date Code
- = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	–0.5 to +7.0	V
V _{IN}	DC Input Voltage	–0.5 to +7.0	V
V _{OUT}	DC Output Voltage	–0.5 to +7.0	V
I _{IK}	DC Input Diode Current V _{IN} < GND	–50	mA
I _{OK}	DC Output Diode Current V _{OUT} < GND	–50	mA
I _O	DC Output Source/Sink Current	±50	mA
I _{CC}	DC Supply Current Per Supply Pin	±100	mA
I _{GND}	DC Ground Current per Ground Pin	±100	mA
T _{STG}	Storage Temperature Range	–65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
T _J	Junction Temperature Under Bias	150	°C
θ _{JA}	Thermal Resistance (Note 1)	496	°C/W
P _D	Power Dissipation in Still Air @ 85°C	252	mW
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 28 to 34	UL 94 V–0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>2000 >200 N/A	V
I _{LATCHUP}	Latchup Performance Above V _{CC} and Below GND at 125 °C (Note 5)	±500	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm–by–1 inch, 2 ounce copper trace no air flow.
2. Tested to EIA/JESD22–A114–A.
3. Tested to EIA/JESD22–A115–A.
4. Tested to JESD22–C101–A.
5. Tested to EIA / JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage Operating Data Retention Only	1.65 1.5	5.5 5.5	V
V _{IN}	Digital Input Voltage (Note 6)	0	5.5	V
V _{OUT}	Output Voltage	0	5.5	V
T _A	Operating Free–Air Temperature	–55	+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate V _{CC} = 1.8 V ± 0.15 V V _{CC} = 2.5 V ± 0.2 V V _{CC} = 3.3 V ± 0.3 V V _{CC} = 5.0 V ± 0.5 V	0 0 0 0	20 20 10 5	ns/V

6. Unused inputs may not be left open. All inputs must be tied to a high or low–logic input voltage level. Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

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DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	V _{CC} (V)	T _A = 25 °C			T _A = -55°C to +125°C		Unit
				Min	Typ	Max	Min	Max	
V _{IH}	Low-Level Input Voltage		1.65	0.75 x V _{CC}			0.75 x V _{CC}		V
			2.3 to 5.5	0.70 x V _{CC}			0.70 x V _{CC}		
V _{IL}	Low-Level Input Voltage		1.65			0.25 x V _{CC}		0.25 x V _{CC}	V
			2.3 – 5.5			0.30 x V _{CC}		0.30 x V _{CC}	
V _{OH}	High-Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OH} = -100 µA	1.65 – 5.5	V _{CC} -0.1	V _{CC}		V _{CC} -0.1		V
		V _{IN} = V _{IH} or V _{IL} I _{OH} = -4 mA	1.65	1.29	1.52		1.29		
		I _{OH} = -8 mA	2.3	1.9	2.15		1.9		
		I _{OH} = -12 mA	2.7	2.2	2.4		2.2		
		I _{OH} = -16 mA	3.0	2.4	2.8		2.4		
		I _{OH} = -24 mA	3.0	2.3	2.68		2.3		
		I _{OH} = -32 mA	4.5	3.8	4.2		3.8		
V _{OL}	Low-Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OL} = 100 µA	1.65 – 5.5			0.1		0.1	V
		V _{IN} = V _{IH} or V _{IL} I _{OH} = 4 mA	1.65		0.08	0.24		0.24	
		I _{OH} = 8 mA	2.3		0.1	0.3		0.3	
		I _{OH} = 12 mA	2.7		0.12	0.4		0.4	
		I _{OH} = 16 mA	3.0		0.15	0.4		0.4	
		I _{OH} = 24 mA	3.0		0.22	0.55		0.55	
		I _{OH} = 32 mA	4.5		0.22	0.55		0.55	
I _{IN}	Input Leakage Current	0 ≤ V _{IN} ≤ 5.5V	0 to 5.5			±0.1		±1.0	µA
I _{OFF}	Power-Off Output Leakage Current	V _{IN} or V _{OUT} = 5.5 V	0			1.0		10	µA
I _{CC}	Quiescent Supply Current	0 ≤ V _{IN} ≤ V _{CC}	5.5			1.0		10	µA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 2.5 nS)

Symbol	Parameter	V _{CC} (V)	Test Condition	T _A = 25 °C			T _A = -55°C to +125°C		Unit
				Min	Typ	Max	Min	Max	
t _{PLH} , t _{PHL}	Propagation Delay, Input to Output	1.65–1.95	R _L = 1 MΩ, C _L = 15 pF	2.0	5.5	18.5	2.0	19	ns
		2.3–2.7	R _L = 1 MΩ, C _L = 15 pF	0.8	3.0	11	0.8	11.5	
		3.0–3.6	R _L = 1 MΩ, C _L = 15 pF	0.5	2.6	7.5	0.5	8.0	
			R _L = 500 Ω, C _L = 50 pF	1.5	3.0	8.5	1.5	9.0	
		4.5–5.5	R _L = 1 MΩ, C _L = 15 pF	0.5	2.2	5.5	0.5	6.0	
			R _L = 500 Ω, C _L = 50 pF	0.8	2.4	7.0	0.8	7.5	
C _{IN}	Input Capacitance	5.5	V _{IN} = 0 V or V _{CC}		4.0				pF
C _{PD}	Power Dissipation Capacitance (Note 7)	3.3	10 MHz		20				pF
		5.5	V _{IN} = 0 V or V _{CC}		26				

7. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption: P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

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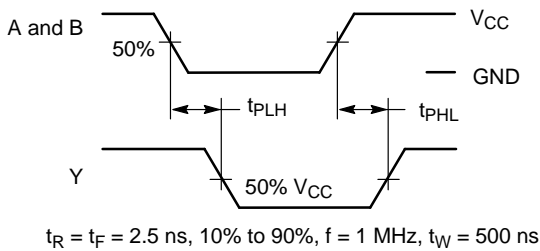


Figure 3. Switching Waveforms

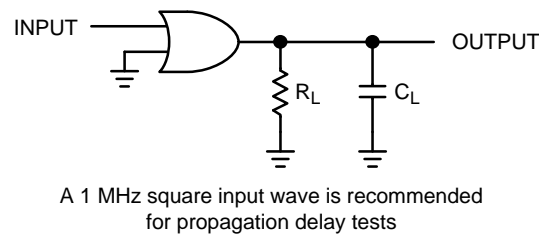


Figure 4. Test Circuit

ORDERING INFORMATION

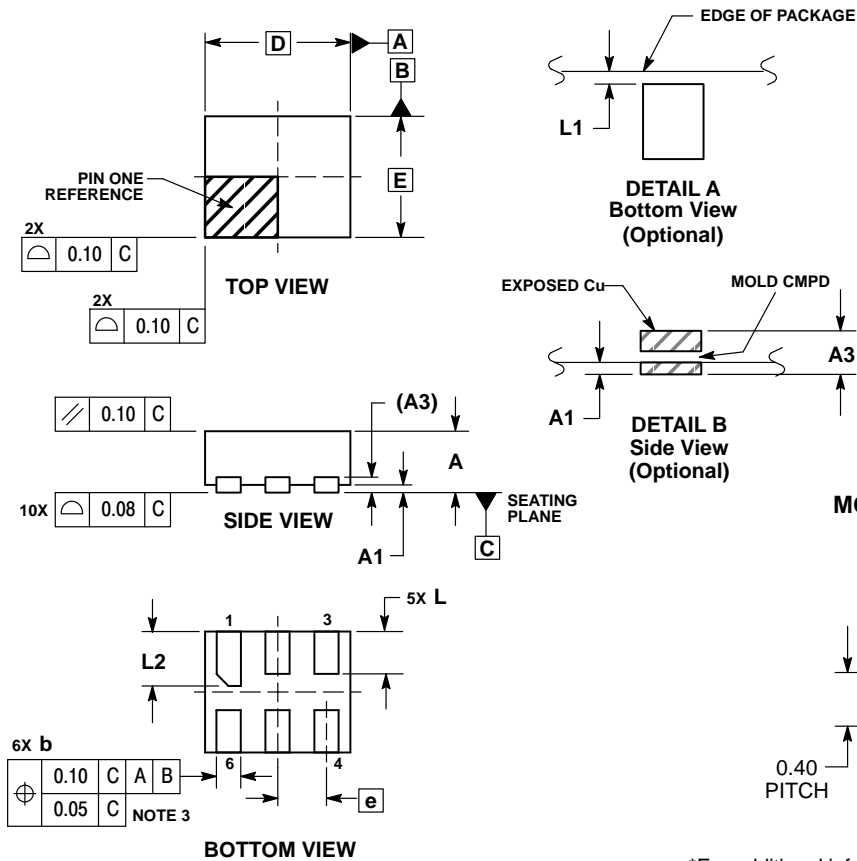
Device	Package	Shipping†
NLX1G332MUTCG In Development	UDFN6, 1.2 x 1.0, 0.4P (Pb-Free)	3000 / Tape & Reel
NLX1G332AMUTCG	UDFN6, 1.45 x 1.0, 0.5P (Pb-Free)	3000 / Tape & Reel
NLX1G332CMUTCG	UDFN6, 1.0 x 1.0, 0.35P (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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PACKAGE DIMENSIONS

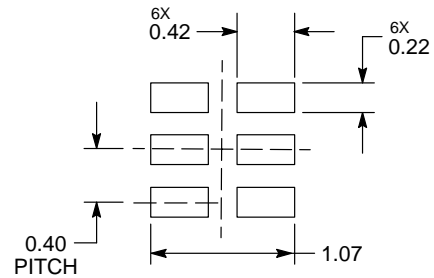
UDFN6, 1.2x1.0, 0.4P
CASE 517AA-01
ISSUE D



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 mm FROM TERMINAL.
 4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

MILLIMETERS		
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.127 REF	
b	0.15	0.25
D	1.20 BSC	
E	1.00 BSC	
e	0.40 BSC	
L	0.30	0.40
L1	0.00	0.15
L2	0.40	0.50

MOUNTING FOOTPRINT*



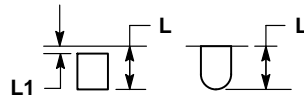
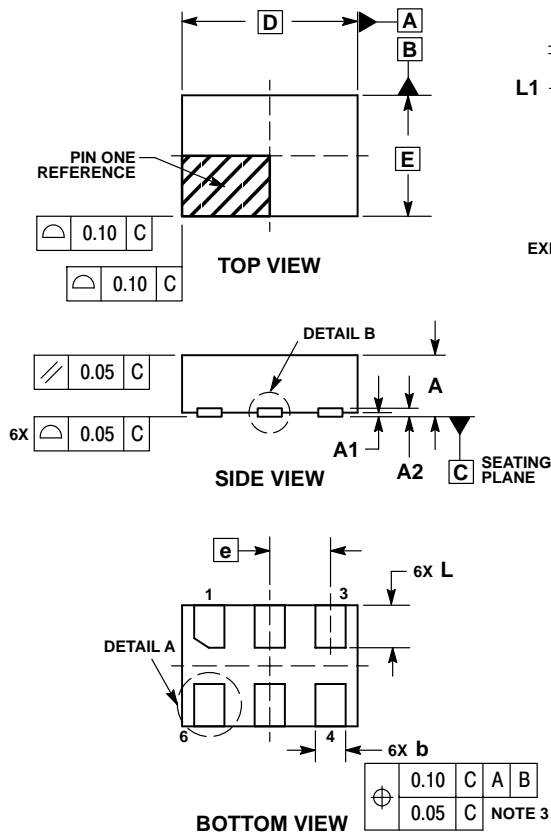
DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

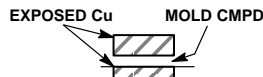
NLX1G332

PACKAGE DIMENSIONS

UDFN6 1.45x1.0, 0.5P
CASE 517AQ
ISSUE O



DETAIL A
OPTIONAL
CONSTRUCTIONS



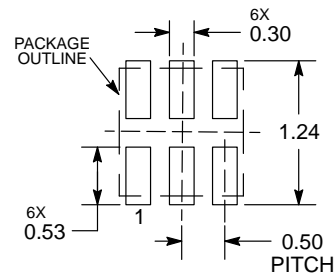
DETAIL B
OPTIONAL
CONSTRUCTIONS

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.

MILLIMETERS		
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A2	0.07 REF	
b	0.20	0.30
D	1.45 BSC	
E	1.00 BSC	
e	0.50 BSC	
L	0.30	0.40
L1	—	0.15

MOUNTING FOOTPRINT



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

